

General Description

The HSP15N25 uses advanced Planar MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

The HSP16N25 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

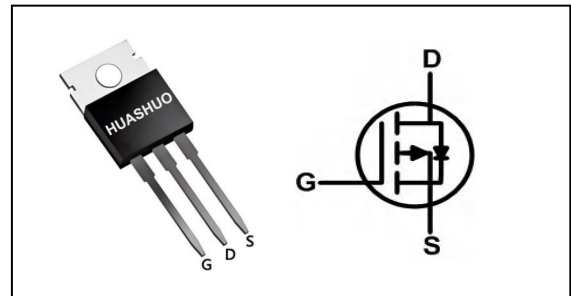
Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench Technology

Product Summary

V_{DS}	250	V
$R_{DS(ON),max}$	250	m Ω
I_D	16	A

TO-220 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	250	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	16	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	7.5	A
I_{DM}	Pulsed Drain Current ²	65	A
EAS	Single Pulse Avalanche Energy ³	140	mJ
I_{AS}	Avalanche Current	16	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	120	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1	$^\circ C/W$



N-Ch 250V Fast Switching MOSFETs

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	250	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =8A	---	220	250	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2	3	4	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =160V, V _{GS} =0V, T _J =25°C	---	---	1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =160V, V _{GS} =0V, T _J =125°C	---	---	5	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±30V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =8A	---	10	---	S
Q _g	Total Gate Charge	V _{DS} =200V, V _{GS} =10V, I _D =-16A	---	23	---	nC
Q _{gs}	Gate-Source Charge		---	9	---	
Q _{gd}	Gate-Drain Charge		---	6.2	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =120V, V _{GS} =10V, R _G =25Ω, I _D =16A	---	13	---	ns
T _r	Rise Time		---	30	---	
T _{d(off)}	Turn-Off Delay Time		---	125	---	
T _f	Fall Time		---	39	---	
C _{iss}	Input Capacitance	V _{DS} =5V, V _{GS} =0V, f=1MHz	---	1289	---	pF
C _{oss}	Output Capacitance		---	149	---	
C _{rss}	Reverse Transfer Capacitance		---	47	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	16	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	65	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =16A, T _J =25°C	---	---	1.4	V
T _{rr}	Reverse Recovery Time	IF= 16A, dI/dt= 100A/μs, T _J =25°C	---	205	---	nS
Q _{rr}	Reverse Recovery Charge		---	1.88	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=-75V,V_{GS}=-10V,L=0.1mH,I_{AS}=-35A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

Fig. 1 $I_D - V_{DS}$

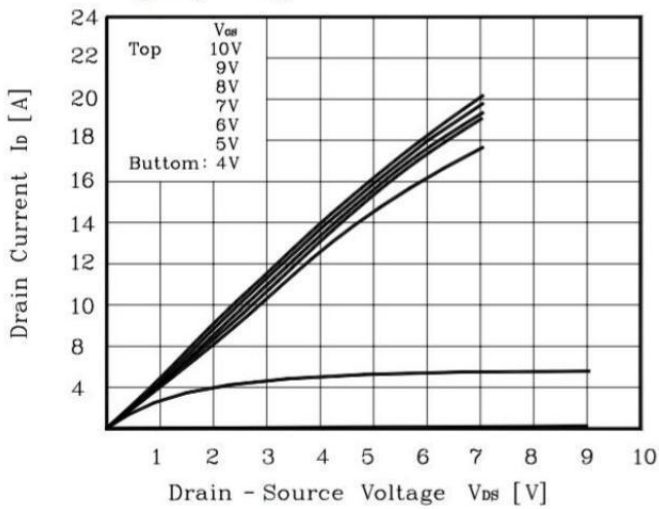


Fig. 2 $I_D - V_{GS}$

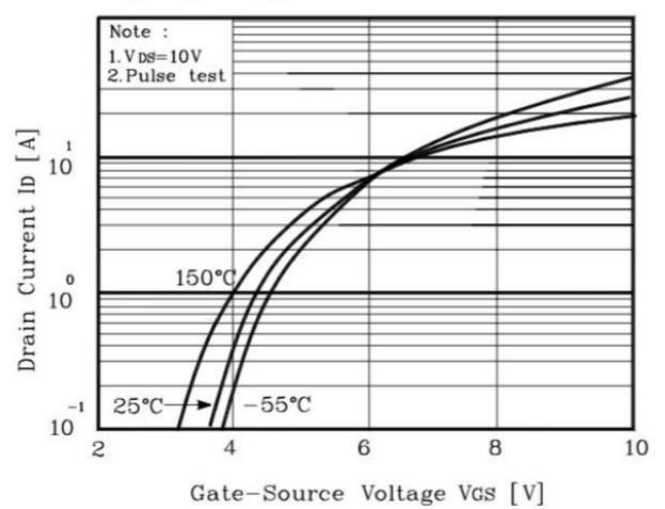


Fig. 3 $R_{DS(on)} - I_D$

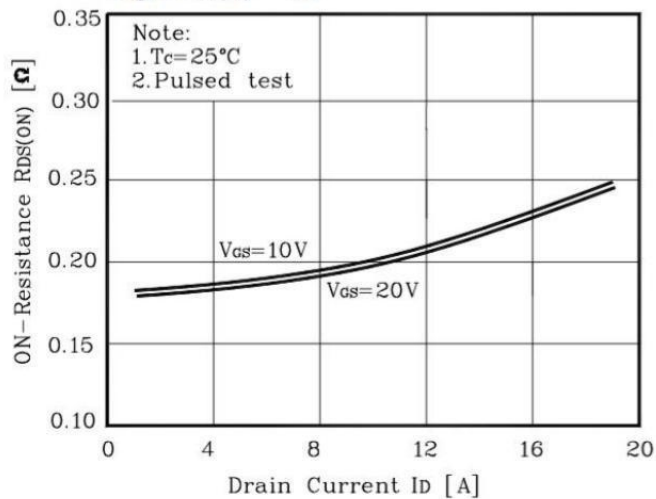


Fig. 4 $I_S - V_{SD}$

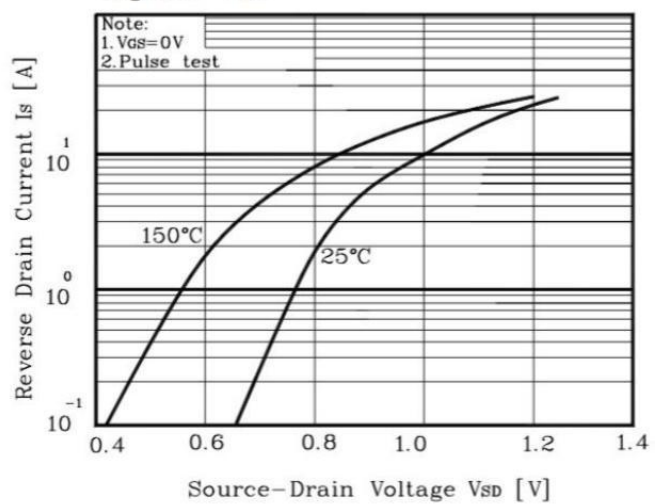


Fig. 5 Capacitance - V_{DS}

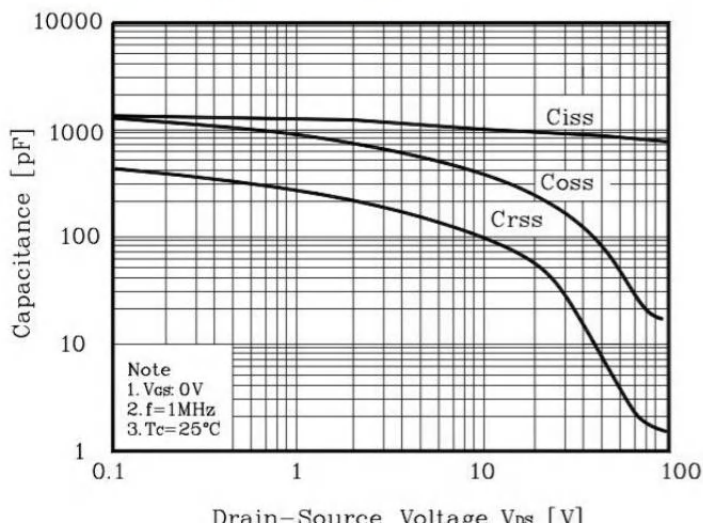
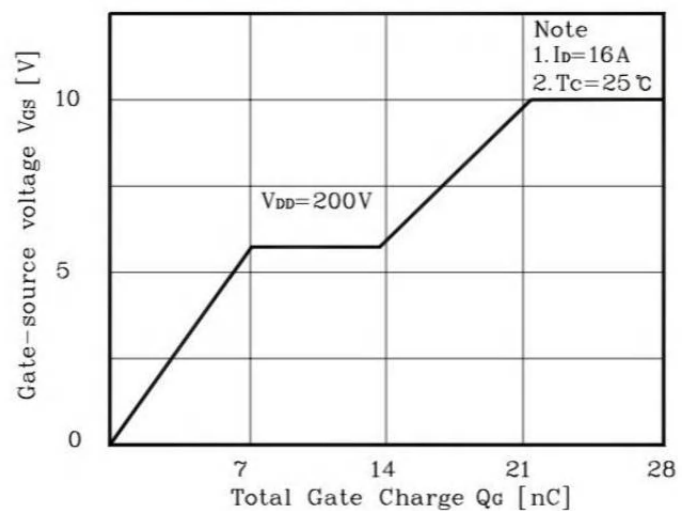


Fig. 6 $V_{GS} - Q_G$





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Fig. 7 $V_{DS} - T_J$

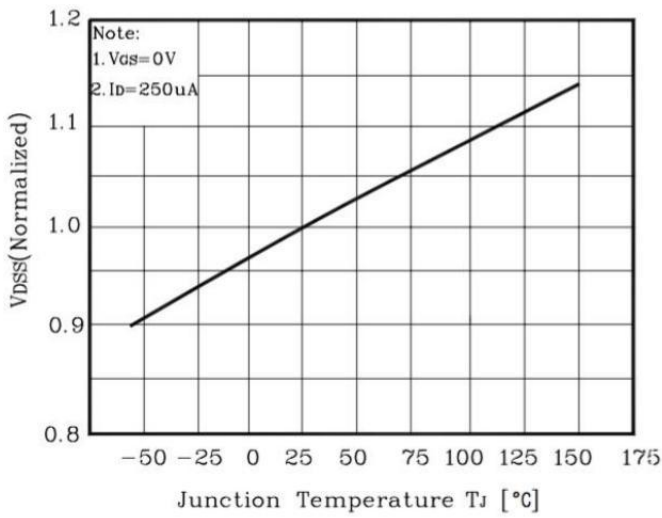


Fig. 8 $R_{DS(on)} - T_J$

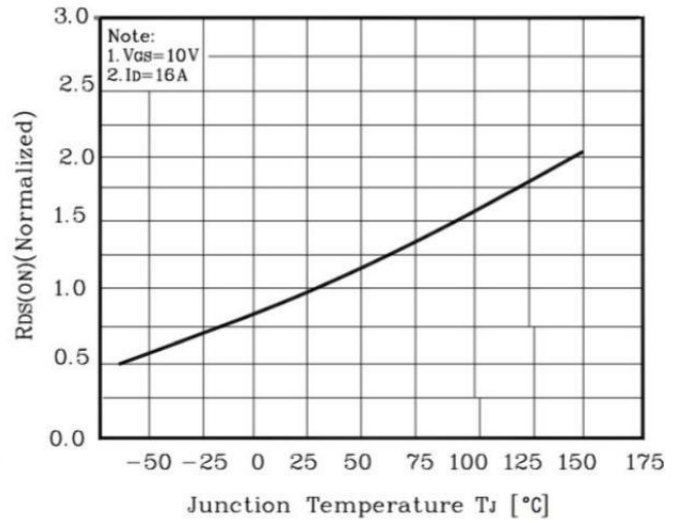


Fig. 9 $I_D - T_C$

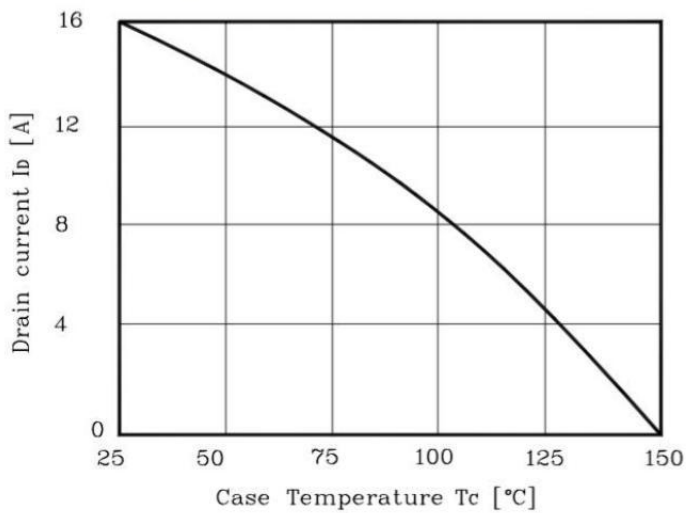
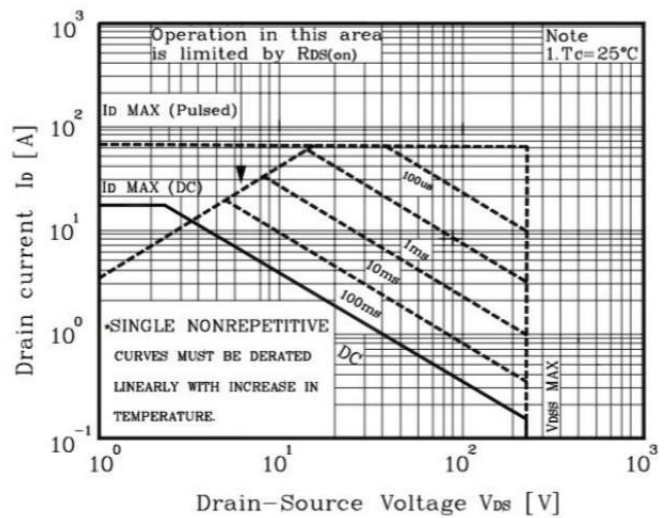


Fig. 10 Safe Operating Area

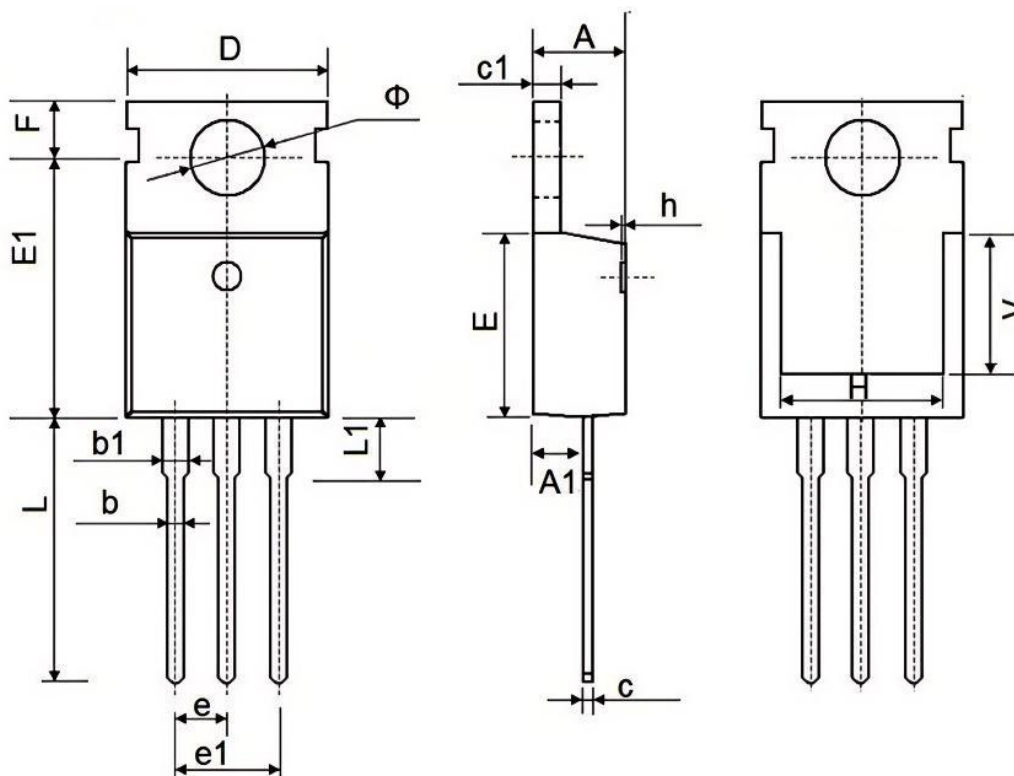




Ordering Information

Part Number	Package code	Packaging
HSP16N25	TO-220	1000/Box

TO-220 Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	2.200	2.600	0.087	0.102
b	0.700	0.950	0.028	0.037
b1	1.170	1.410	0.046	0.056
C	0.450	0.650	0.018	0.026
c1	1.200	1.400	0.047	0.055
D	9.600	10.400	0.378	0.409
E	8.8500	9.750	0.348	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.750	14.300	0.502	0.563
L1	2.850	3.950	0.112	0.156
V	7.500 REF.		0.295 REF.	
Φ	3.400	4.000	0.134	0.157

HSP16N25 Marking:

